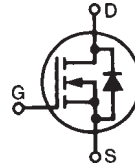
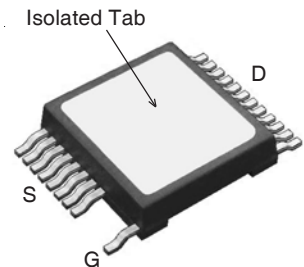
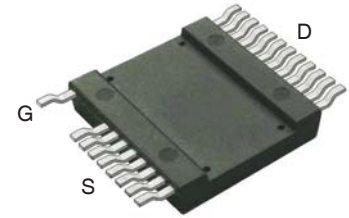


**Polar™ HiperFET™  
Power MOSFET**
**MMIX1F40N110P**

(Electrically Isolated Tab)

 N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Rectifier


$$\begin{aligned} V_{DSS} &= 1100V \\ I_{D25} &= 24A \\ R_{DS(on)} &\leq 290m\Omega \\ t_{rr} &\leq 300ns \end{aligned}$$


 G = Gate      D = Drain  
S = Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1100	V
$V_{DGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1M\Omega$	1100	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	24	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$	100	A
$I_A$	$T_C = 25^\circ\text{C}$	20	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	2	J
$dv/dt$	$I_S \leq I_{DM}, V_{DD} \leq V_{DSS}, T_J \leq 150^\circ\text{C}$	15	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	500	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, 1 Minute	2500	V~
$F_C$	Mounting Force	50..200 / 11..45	N/lb.
<b>Weight</b>		8	g

**Features**

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Substrate
  - Excellent Thermal Transfer
  - Increased Temperature and Power Cycling Capability
  - High Isolation Voltage (2500V~)
- Low Intrinsic Gate Resistance
- Low Package Inductance
- Fast Intrinsic Rectifier
- Low  $R_{DS(on)}$  and  $Q_G$

**Advantages**

- High Power Density
- Easy to Mount
- Space Savings

**Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- Pulse Power Applications
- Discharge Circuits in Lasers Pulsers, Spark Igniters, RF Generators
- DC-DC converters
- DC-AC inverters

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V, I_D = 3mA$	1100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1mA$	3.5		6.5 V
$I_{GSS}$	$V_{GS} = \pm 30V, V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			50 $\mu\text{A}$ 3 mA
$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$ , Note 1			290 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}, I_D = 20\text{A}$ , Note 1	20	32	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		19	nF
$C_{oss}$			1070	pF
$C_{rss}$			46	pF
$R_{Gi}$	Gate Input Resistance		1.65	$\Omega$
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 20\text{A}$ $R_G = 1\Omega$ (External)		53	ns
$t_r$			55	ns
$t_{d(off)}$			110	ns
$t_f$			54	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 20\text{A}$		310	nC
$Q_{gs}$			95	nC
$Q_{gd}$			142	nC
$R_{thJC}$				0.25 $^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

**Source-Drain Diode**

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			40 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			160 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 20\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			300 ns
$Q_{RM}$			2.2	$\mu\text{C}$
$I_{RM}$			16.0	A

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

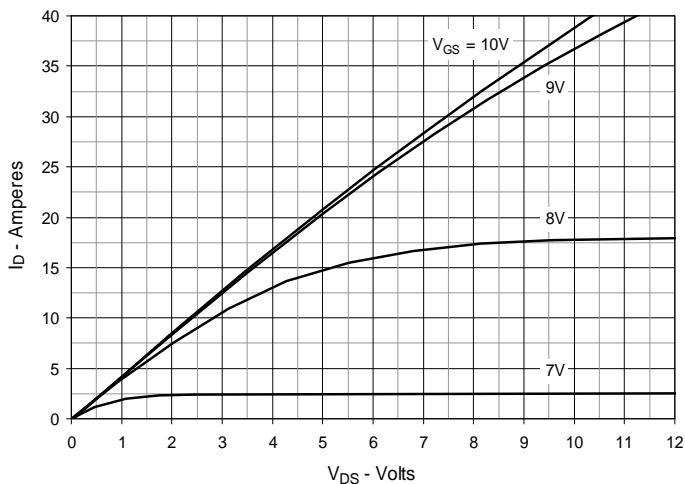
**ADVANCE TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

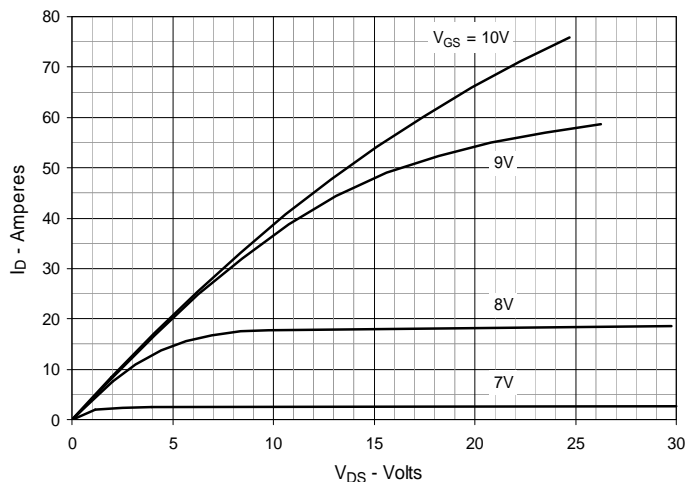
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
by one or more of the following U.S. patents:	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

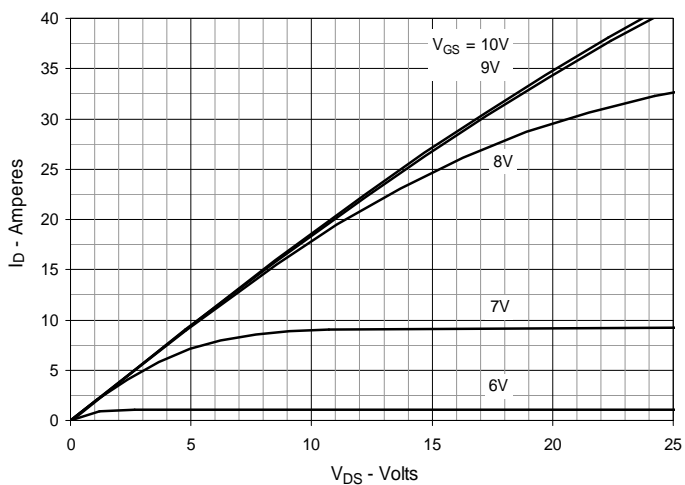
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



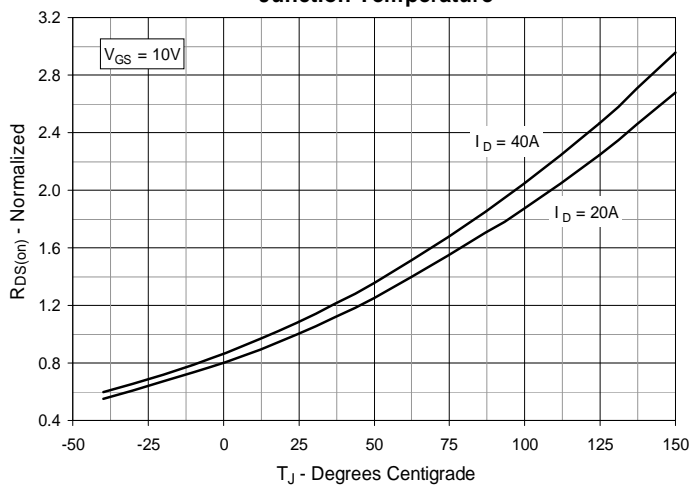
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



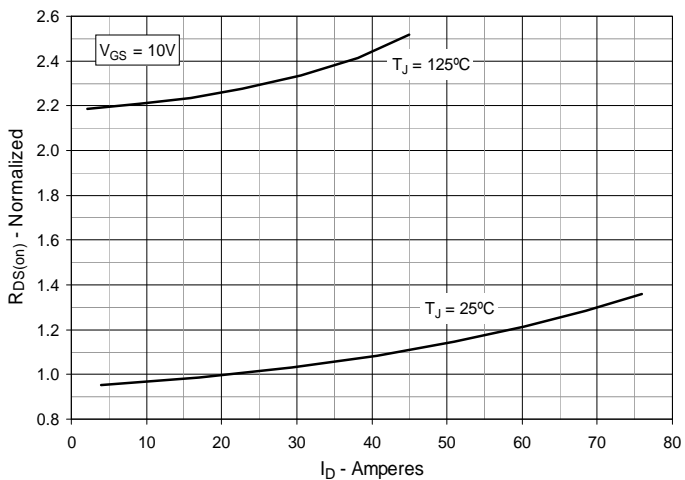
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



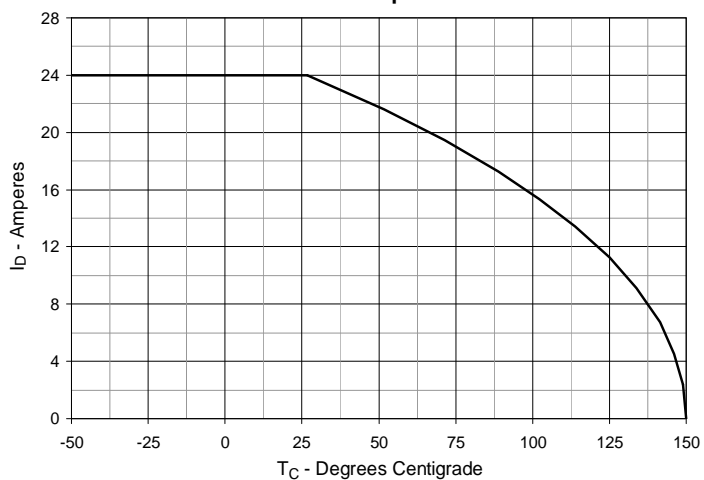
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 20A$  Value vs. Junction Temperature**



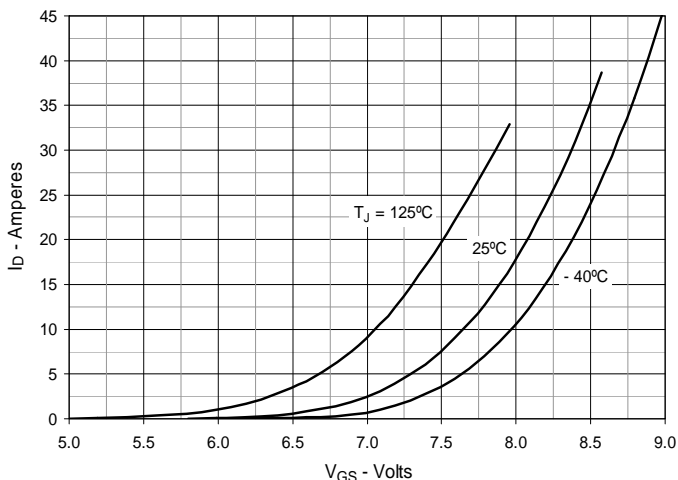
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 20A$  Value vs. Drain Current**



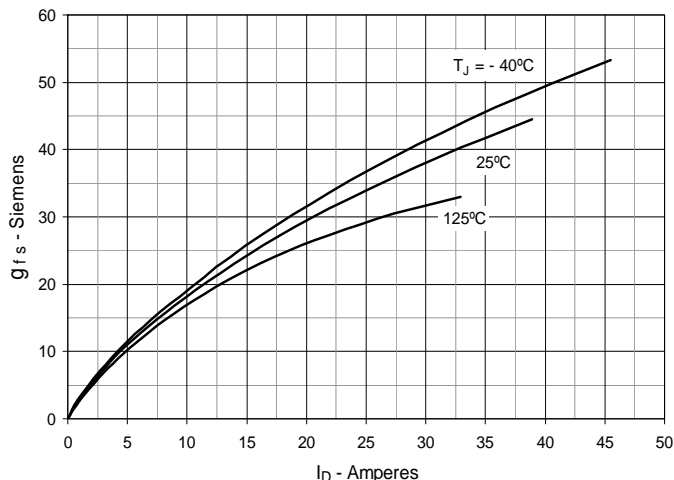
**Fig. 6. Maximum Drain Current vs. Case Temperature**



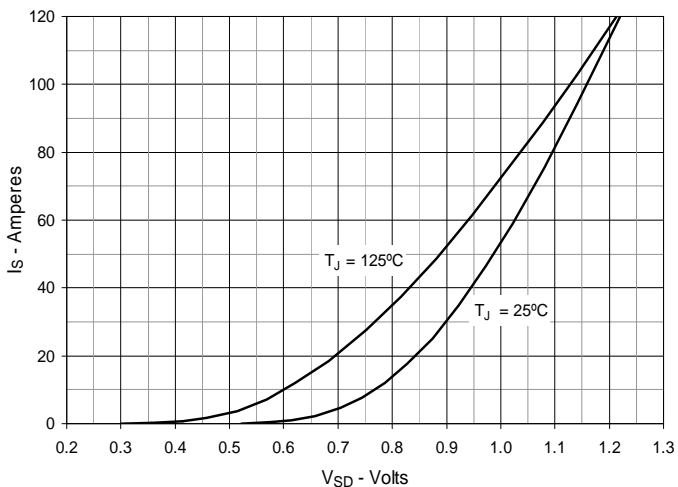
**Fig. 7. Input Admittance**



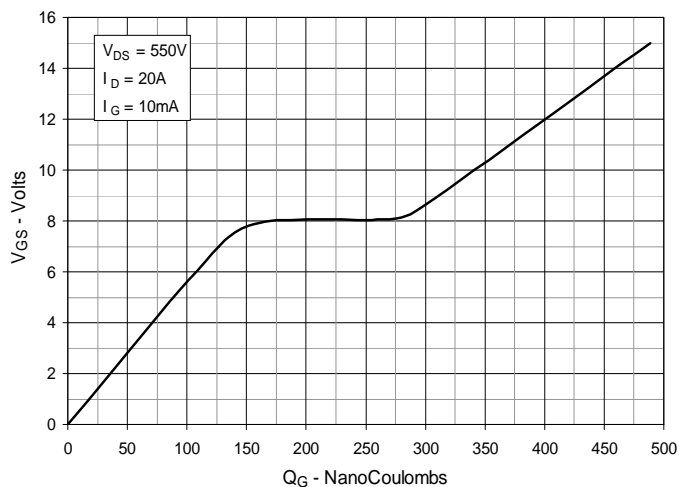
**Fig. 8. Transconductance**



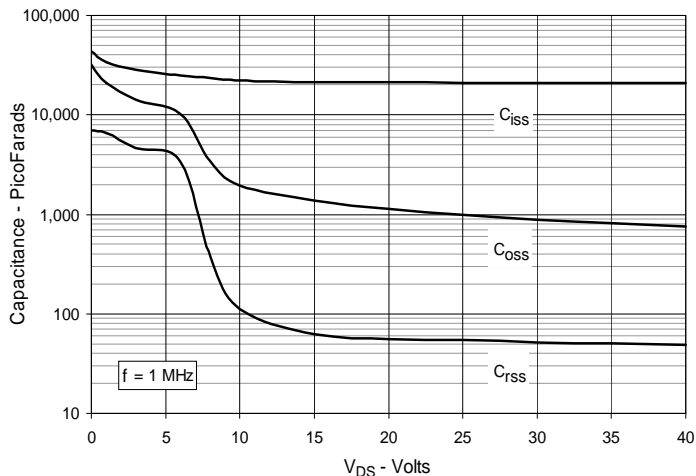
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

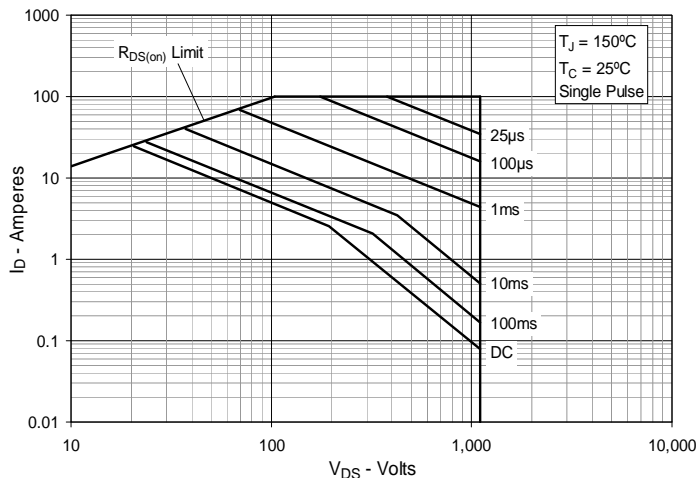
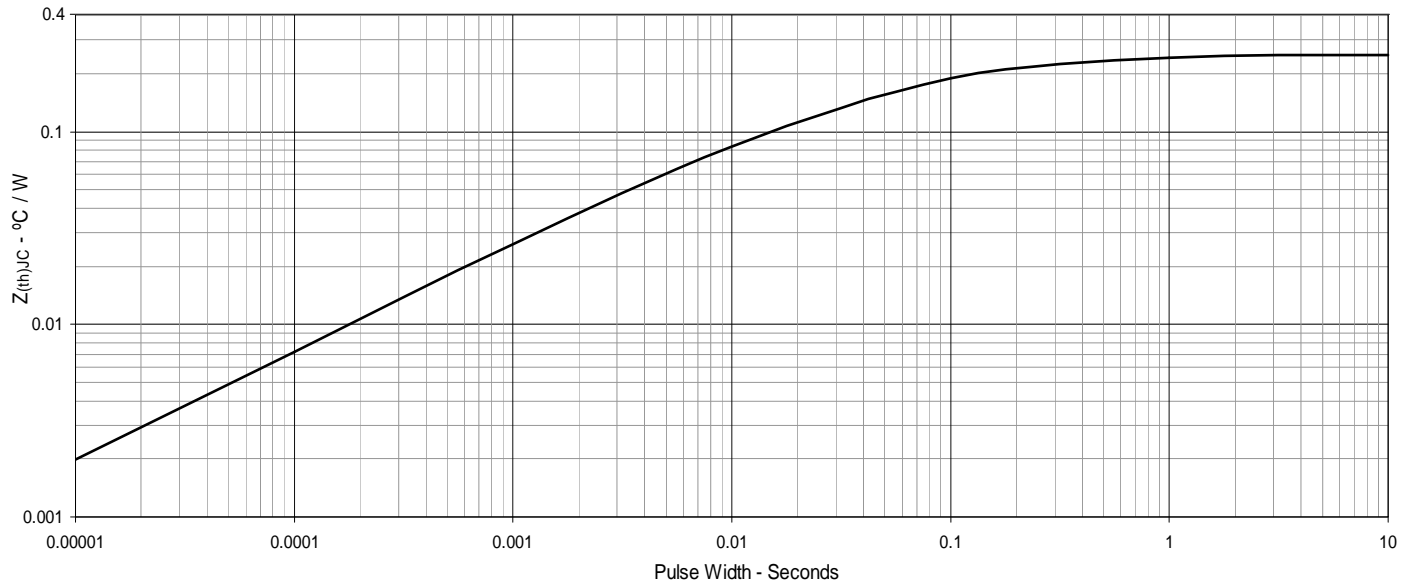
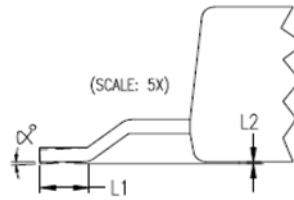
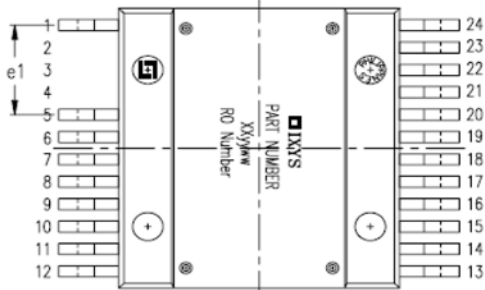
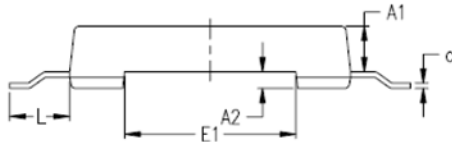
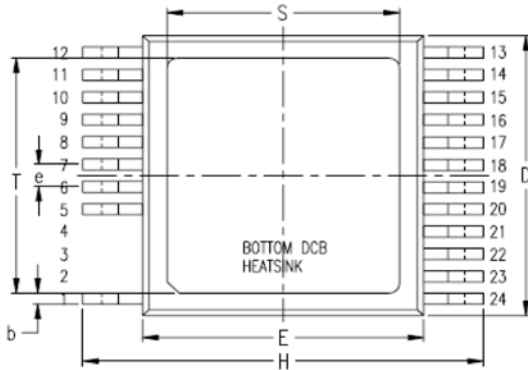


Fig. 13. Maximum Transient Thermal Impedance





SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.209	.224	5.30	5.70
A1	.154	.161	3.90	4.10
A2	.055	.063	1.40	1.60
b	.035	.045	0.90	1.15
c	.018	.026	0.45	0.65
D	.976	.994	24.80	25.25
E	.898	.915	22.80	23.25
E1	.543	.559	13.80	14.20
e	.079 BSC		2.00 BSC	
e1	.315 BSC		8.00 BSC	
H	1.272	1.311	32.30	33.30
L	.181	.209	4.60	5.30
L1	.051	.067	1.30	1.70
L2	.000	.006	0.00	0.15
S	.736	.760	18.70	19.30
T	.815	.839	20.70	21.30
∞	0	4'	0	4'

**PIN:** 1 = Gate  
 5-12 = Source  
 13-24 = Drain